

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.  
244221US-2 SRD DIVSERIAL NO. 10/691,706  
NEW DIV APPLICATION

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT  
Daisaburo TAKASHIMAFILING DATE  
HEREWITH 10/24/03GROUP  
UNASSIGNED 2818

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TP	AA	5,345,415	09/06/94	Hironobu NAKAO, et al.	365	145	
	AB	5,303,182	04/12/94	Hironobu NAKAO, et al.	365	145	
	AC	5,956,655	9/1999	suzuki et al	455	566	
	AD	5,029,128	7-1991	TODA	365	145	
	AE	5,307,304	4/1994	SAITO ET AL	365	145	
	AF	5,373,463	12/1994	JONES, JR.	365	145	
	AG	5,383,150	1/1995	NAKAMURA ET AL	365	145	
	AH	5,517,445	5/1996	IMAI ET AL	365	145	
↓	AI	5,592,646	1/1997	THOMAS	365	145	
	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
TP	AO	07-176195	07/14/95	JAPAN (W/ ENGLISH ABSTRACT)		✓
	AP	95-1776	01/03/95	REPUBLIC OF KOREA		✓
	AQ	3-40298	2/1991	JAPAN		✓
↓	AR	6-140597	5/1994	JAPAN		✓
	AS					
	AT					
	AU					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

TP	AV	K. Takeuchi, et al., "Half-Vcc Plate Nonvolatile DRAMs with Ferroelectric Capacitors", Jeece Trans, Electron., Vol. E79-C, No. 2, Feb. 1996, pp. 234-242.
	AW	K. Sunouchi, et al., "A surrounding Gate Transistor (SGT) Cell for 64/256Mbit DRAMs", IEDM, Dec. 1989, pp. 23-26.
	AX	T. Hasegawa, et al., "An Experimental DRAM with a NAND-Structured Cell", IEEE International Solid-State Circuits Conference, Feb. 24, 1993, pp. 46-47.
	AY	T. Sumi et al., "A 256kb Nonvolatile Ferroelectric Memory at 3V and 100ns", IEEE International Solid-State Circuits Conference, Feb. 18, 1994, pp. 268-269
↓	AZ	H. Koike, et al., "A 60ns 1Mb Nonvolatile Ferroelectric Memory with Non-Driven Cell Plate Line Write/Read Scheme", IEEE International Solid-State Circuits Conference, Feb 10, 1996, pp. 368-369

☐ Additional References sheet(s) attached

Examiner Trong Phan

Date Considered 3/3/04

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.